

IN THE CLAIMS:

(Claims 1-16 have been cancelled)

Sub C1
B1

17.(Original) A memory system comprising:
a plurality of memory groups, each of said memory groups comprising a plurality of memory sectors, each of said memory sectors comprising a plurality of memory cells;

a plurality of group tags, each of said group tags corresponds to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are erasable; and

a plurality of sector tags, each of said sector tags corresponds to a memory sector, each of said sector tags indicating whether the memory cells under the corresponding memory sector are erasable,

wherein all the memory cells belonging to one memory sector are erasable when either the corresponding sector tag or the corresponding group tag of the memory sector is set;

wherein any combination of memory sectors in a memory group can 15 be simultaneously erased, and any combination of the memory groups can be simultaneously erased.

18.(Original) The memory system according to Claim 17, wherein the number of memory sectors in each memory group is configurable.

19.(Original) The memory system according to Claim 18, wherein the corresponding sectors in each memory group is calculated in real time.

20.(Original) The memory system according to Claim 17, wherein the number of memory cells in each memory sector is configurable.

21.(Original) The memory system according to Claim 20, wherein the corresponding memory cells in each memory sector is calculated in real time.

22.(Original) The memory system according to claim 17 is a flash memory.

23.(Original) A memory system comprising:
a plurality of memory groups, each of said memory groups comprising a plurality of memory cells;
a plurality of group tags, each of said group tags corresponding to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are write protected; and
wherein any combination of the memory groups can be write protected.

B/ 24.(Original) The memory system according to Claim 23, wherein the number of memory cells in each memory group is configurable.

25.(Original) The memory system according to Claim 23, wherein the corresponding cells in each memory group is calculated in real time.

26.(Currently Amended) The memory system according to claim ~~22~~ 23 is a flash memory.